Nanomate Premium

For SiC finish process

Nanomate
Premium

Suitable for wafer grinding of semiconductor power device

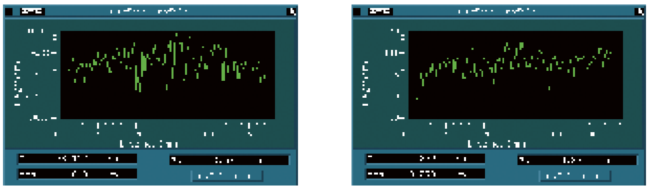
Combining diamond grit and vitrified bond with suitable ratio to obtain best grit clearance for efficient grinding. Continuous grinding of monocrystal SiC is now available.

Especially, superabrasive wheel can process with same feed rate as the one for silicon wafer grinding to obrain extremely smooth surface.

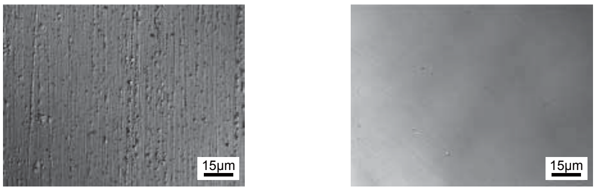
☐Grit size and work surface (SiC wafer)

●SD3000 (feed 40μm/min) ●SD8000 (feed 20μm/min)

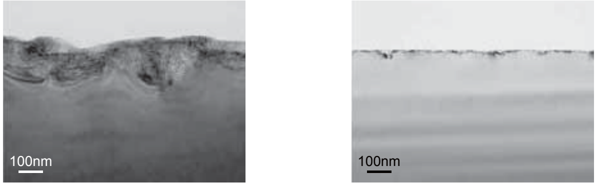
Surface roughness



Surface of workpiece



Damage of surface



For SiC and Sapphire rough process

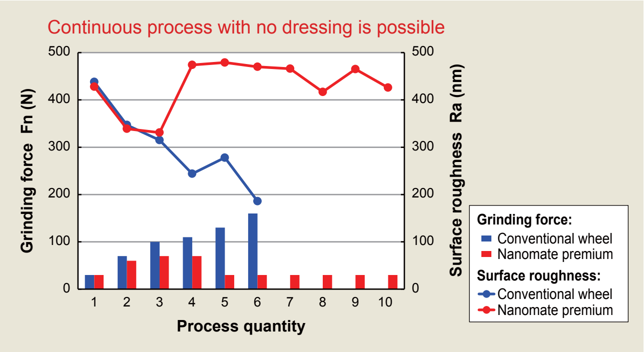
Nanomate
Premium

Suitable for rough and semi-finish grinding of semiconductor power device

Newly developed vitrified bond for rough process has high grit retention and pore which realize high efficient continuous process.

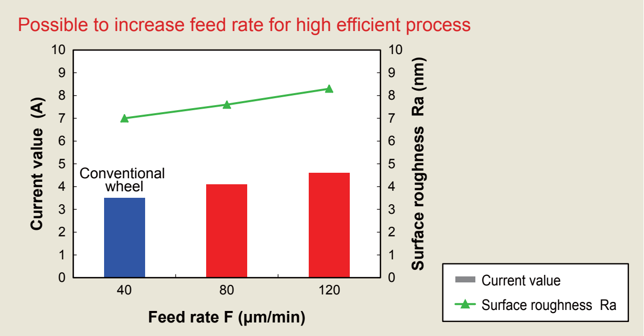
Suitable for hard-to-cut material such as sapphire and SiC and can feed 2 to 3 times compared to conventional wheel.

☐Grinding result of 4 inch sapphire wafer



Normal force and surface roughness (Spec : SD400)

☐High efficient grinding results of 3 inch SiC wafer



Current value and surface roughness (Spec : SD2000)